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02-11-2017	7		Final Report				15-Jul-2016 - 14-Jul-2017	
4. TITLE AN	ND SUBTITLE				5a. C0	ONTR	RACT NUMBER	
Final Report	rt: DURIP: Ar	n Ultrafast Tes	stbed for Comprehe	ensive	e W911	INF-	16-1-0140	
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RPPR Final Report

as of 17-Nov-2017

Agency Code:

Proposal Number: 68602ELRIP INVESTIGATOR(S):

Agreement Number: W911NF-16-1-0140

Name: Ali Adibi Ph.D. Email: ali.adibi@ece.gatech.edu Phone Number: 4043852738 Principal: Y

Organization: Georgia Tech Research Corporation Address: 505 Tenth Street NW, Atlanta, GA 303320420 Country: USA DUNS Number: 097394084 EIN: 580603146 Report Date: 14-Oct-2017 Date Received: 02-Nov-2017 Final Report for Period Beginning 15-Jul-2016 and Ending 14-Jul-2017 Title: DURIP: An Ultrafast Testbed for Comprehensive Characterization of Photonics, Electronic, and Optoelectronic Properties of Inegrated Nanophotonic Structures Begin Performance Period: 15-Jul-2016 End Performance Period: 14-Jul-2017 Report Term: 0-Other Submitted By: Volker Sorger Email: sorger@gwu.edu Phone: (202) 994-7186

Distribution Statement: 1-Approved for public release; distribution is unlimited.

STEM Degrees:

STEM Participants:

Major Goals: In this DURIP program an ultrafast characterization testbed for the characterization of high-speed integrated photonic devices such as high-speed integrated photonic modulators and detectors was developed.

Accomplishments: Please see the attached report file.

Training Opportunities: Nothing to Report

Results Dissemination: Nothing to Report

Honors and Awards: Nothing to Report

Protocol Activity Status:

Technology Transfer: Nothing to report

PARTICIPANTS:

Participant Type: PD/PI Participant: Ali Adibi Person Months Worked: 1.00 Project Contribution: International Collaboration: International Travel: National Academy Member: N Other Collaborators:

Funding Support:

RPPR Final Report as of 17-Nov-2017

Final Report: DURIP Grant Number: W911NF1610140 Sponsor: Army research Office (ARO), PI: Ali Adibi Program Title: An Ultrafast Testbed for Comprehensive Characterization of Photonics, Electronic, and Optoelectronic properties of Integrated Nanophotonic Structures

I. Abstract

In this DURIP program an ultrafast characterization testbed for the characterization of highspeed integrated photonic devices such as high-speed integrated photonic modulators and detectors was developed. A major requirement in performing successful research in this field is the availability of ultra-fast optoelectronic characterization tools that facilitate the study of ultrafast low-power devices and systems (e.g., modulators, switches, detectors). This characterization setup has been an enabling platform for development of ultrafast, compact, and low-power high speed optoelectronic devices under several DoD grants, including ARO-funded program for the development of ultrafast graphene-based modulators and several other programs supported by ONR, DARPA, and AFOSR. The developed characterization testbed has provided Adibi's group at Georgia-Tech with an integrated ultrafast characterization tools, which has greatly enhanced its capability in fast and accurate characterization of high-speed integrated optoelectronic for the study of the device physics and high-speed device optimizations. The tool is also available to other research group at Georgia-Tech and outside researches as a shared facility.

II. Characterization Setup and Budget

The high speed setup is realized by integrating high-speed characterization equipment to an already available photonic characterization setup. The following table details of the spent budget and the list of purchased equipment that are used in this setup. The extra \$231.14 over the \$145,000 budget was paid from the PI's chair account in the School of ECE, Georgia Tech.

Item	Part #	Description	Manufacturer	Vendor	Quant.	Unit(\$)	Price (\$)
1	86100D	Infiniium DCA-X Oscilloscope Main- frame	Keysight	Keysight	1	\$8,622.16	\$8,622.16
2	N1045A	60 GHz 2/4 Port Electrical Remote Sampling Head	Keysight	Keysight	1	\$28,716.88	\$28,716.88
3	M8195A	Arbitrary Wave- form Generator 65GSa/s	Keysight	Keysight	1	\$85,866.87	\$85,866.87
4	i50-GS-150	50 GHz infinity probe	Cascade	Cascade	1	\$ 920.00	\$ 920.00
5	IO-H-1550FC	IR Fiber Optic Iso- lator with SM Fiber	Thorlabs	Thorlabs	2	\$188.00	\$376.00
6	S7FC1013S	Benchtop Fiber- Coupled Semicon- ductor Optical Am- plifiers	Thorlabs	Thorlabs	1	\$2,720.00	\$2,720.00
7	SPA-180-37- 01-SMAA	300 MHz to 18 GHz, Medium Power Broadband Amplifier	Fairview Mi- crowave	Fairview Microwave,	1	\$4,999.00	\$4,999.00
8		Cable and connect- ors		Fairview Microwave	1	\$1,436.23	\$1,436.23
9	XPDV2320R- VM-FP	50 GHz single pho- todetector	Finisar	XSoptix	1	\$4,396.00	\$4,396.00
10	2614B	Source Measure- ment Unit (SMU)	Keithley	Microlease	1	\$6,364.00	\$6,364.00
11 Total	2614B-probe	SMU Probe	Keithley	Microlease	1	\$814.00	\$814.00 \$145,231.14
Total							φ 14 5,251.14

III. Supporting Information

III.A. High-speed optoelectronic characterization testbed for integrated nanophotonic structures

Figure 1 shows the schematic of the realized characterization testbed, which is used to measure the optical, electronic, and optoelectronic properties of an integrated photonic structure. The sample under test (SUT) placed on a highly functional 5D stage (with full positioning control over translation in three directions, rotation, and tilt. It is also monitored by a spatially designed microscope from the top that is connected to a camera to monitor different devices fabricated in the SUT (typically, 10s to 100s of devices are fabricated in a single substrate). On the optical side, the input light from a tunable laser source (in the optical communications wavelength window of 1450-1650 nm) is coupled into an integrated photonic waveguide on a chip either from the top (through a grating) or from the side (through a butt-coupled fiber). The light in the input waveguide will go through the photonic structure and will be coupled out either from the side (to a butt-coupled fiber) or from the top (through a grating into a fiber). The output light is analyzed by an ultra-fast detector or an ultrafast oscilloscope as shown in Figure 1. The testbed is capable of both input/output coupling formats with minimal modifications. By sweeping the wavelength of the input laser, the spectral characteristic of the device (e.g., resonance properties of a resonator or the transfer function of a filter) can be studied.

On the optoelectronic side, the electronic signal for modulating, tuning, or controlling the optical signal comes from a fast arbitrary wave generator (AWG) (65 GS/s M8195A Keysight), and it is applied to the photonic structure after the amplification by power amplifier (30 dBm Fairview Microwave SPA-180-37-01-SMAA) through the high speed probes (50 GHz Infinite Cascade i50-GS-150) as shown in Figure 1. The output optical signal of the nanophotonic (or plasmonic) is measured by first amplifying the optical signal using a low-noise optical semiconductor amplifier (SOA, 14 dBm gain Thorlabs S7FC1013S) and then detected by a high speed detector (50GHz, Finisar XPDV2320R-VM-FP). Finally, the output signal is sampled and detected using a high-speed sampling oscilloscope (60 GS/s Keysight 86100D with N1045A sampling head), which can provide time-domain and spectral information such as eye diagram and spectral transfer function of the device. The testbed in Figure 1 can also be used to characterize the electronic properties (e.g., current-voltage characteristics, resistance measurement, and capacitance measurement) of the integrated structures using the source measurement unit (SMU Keithley 2614B). Such measurements are very important in working with emerging materials such as graphene where the electronic properties (e.g., conductivity) have profound effects on the optoelectronic characteristics of the device (e.g., modulation speed of a photonic modulator). The electronic characterization is performed by using two high-speed probes for applying the desired voltage and measuring the resulting current. The developed testbed enables to characterize different electronic, (passive) photonic, and (active) optoelectronic properties of an integrated optoelectronic device/system. The implementation of the proposed set up was based on integration of high-speed RF/microwave signal generation/measurement equipment acquired through this DU-RIP program funding with a scanning laser characterization setup for integrated photonic devices that was already available in Adibi's lab. Adibi's lab is also equipped with a series on other high speed characterization equipment such as high-speed spectrum analyzers (20 GHz) and Network Analyzer (6 GHz) that can be used for supplementary characterizations.

The implemented high-speed characterization setup provides a high flexibility that can be used for different characterization configuration for different optoelectronic devices. Figure 2 shows the schematic of an example of such configurations for characterization of a high-speed modulators. Very similar architecture with the application of a wideband off-chip modulator can be used to characterize high-speed integrated photodetector structures or to measure the response of a high-speed optical signal processing platform. The same architecture also can be used to characterize high-speed optoelectronic systems such as optoelectronic oscillators (OEO) or high-speed optical signal processing systems. The same characterization system with a different configuration also ca be used to characterize all-optical signal modulation and switching based on nonlinear integrated optoelectronic devices. The high flexibility of the proposed testbed along with the ability to excite and detect the signals at very high speeds make the proposed testbed a unique tool that can facilitate the study of several state-of-the-art integrated photonic structures that are



Figure 1. Schematic of the realized high-speed characterization setup with multi-contact and high-speed probes based on tapered fiber or grating input/output coupling. The output light from a wideband tunable laser, amplified by an EDFA, is used to excite the integrated optical structure through a tapered fiber or grating coupler. The output of the integrated photonic structure is amplified using as OSA and then coupled to a high-speed photodetector. The optoelectronic properties of the high-speed integrated photonic device including, the transmission spectrum and input/output characteristic of the integrated photonic device, I/V characteristic of the optoelectronic devices, the optoelectronic transfer function of the device is measured under different applied electrical voltages to the device. The temperature of the devices is controlled using a TEC with heating and feedback control. The RF/Microwave output of the AWG is amplified by a power amplifier and is applied to the optoelectronic device and output of the detector is measured by an ultra-wideband and low-jitter sampling oscilloscope.

of high demand for DoD applications. In addition, the proposed testbed can be utilized for the characterization of a large variety of electronic and photonic structures beyond integrated optoelectronic system.

III.B. Example of the characterization results for high-speed photonic device characterization

The developed characterization setup in Figure 2 was used to characterizes different modulators fabricated in our group including a low-power and high-speed modulator based on hybrid Si/SiN material platform (Figure 3.a). The developed hybrid Si/SiN modulator integrates high Q resonators in SiN with high-speed phase modulator in Si based carrier dispersion in vertical depletionmode PN-junction-based modulators in Si waveguide to develop high-speed, low-power, and highly linear modulators based coupling modulation. The characterized devices have Q factors in the range of 7×10^4 to 2.1×10^5 . The high RF characterization is done sing the setup in Figure 2, The isolated insertion loss of the modulator device is measured to be between 3 to 6 dB depending on the modulation depth level, and additional insertion loss is due to the input/output grating losses, which are not necessarily optimized to work at 1550 nm SCL telecom band. The setup is built in the synchronous mode, in which a reference clock synchronizes the bit pattern generated by AWG and the digital sampling scope. The AWG can generate different PRBS patterns, and here we mainly used NRZ PRBS (27-1 pattern) with tunable speed through clocking. As the design of the modulator implies, the device can be characterized in on-off-keying (OOK) mode, and therefore the detection can be simplified to use a high-speed photodetector directly fed into the sampling scope through a transimpedance amplifier (TIA) stage for electronic signal amplification and matching.



Figure 162. Schematic of the high-speed characterization setup for measurement of the response of a high speed optoelectronic devices. In this schematic the transmission amplitude of an integrated high-speed modulator is measured using a direct detection schema. Similar configuration can be used for coherent detection of the output signal by mixing the optical signal with local oscillator (LO) laser before detection.

A typical eye diagram result of the device is depicted in Figure 3(b). Here, the measurement is performed at 10 Gbaud/s OOK input signal. The microresonator Q factor of the device under test is measured to be 1.55×10^5 , which leads to the 3-dB bandwidth limit of 1.26 GHz if the cavity

modulation was employed. Figure 3(c) shows the corresponding S_{21} measurement of the EO device, in which the 3-dB bandwidth is located well above 10 GHz. This manifests the successful demonstration of coupling modulation for the device, as well as the RC bandwidth of the PN junction exceeding 10 GHz. We believe that the device is capable of working beyond 10 GHz if the RC limit is addressed through revised PN junction design to reduce parasitic capacitances. BER is also computed through eye diagram Q factor measurements, with the eye Q value of

3.087. The corresponding BER is 1.02×10^{-3} accordingly, which is well below hard decision FEC limit. The increased value of noise is mainly introduced through SOA, which is added to compensate the insertion loss of unoptimized I/O grating couplers. The SOA can be eliminated if the design of I/O ports is optimized, hence opening the path for PAM modulations and enabling higher signal rates.

III.C. The impact of the developed testbed on the past, current, and future ARO-funded research

Adibi is h PI of the ARO-funded research entitled: Compact, Low-power, and High-speed Graphenebased Integrated Modulator Technology. This project is focused on the realization of a new class of modulators based on hybrid silicon-graphene (HSG) material platform. By taking advantage of the high carrier mobility and the strong plasma dispersion effect of graphene combined with high light confinement in compact Si-photonic devices, this ARO-funded project targets modulators with modulation speeds exceeding 100 Gb/s and sub-100 fJ/bit energy consumption.

Successful development of the proposed modulators



Figure. 3. (a) The dark-field micrograph image of the fabricated modulator. (b) Measured eye diagram of PRBS (27-1 pattern) at 10 Gb/s generated using AWG. (c) The measured EOE S21 of the modulator after direct detection. The curve is normalized to S21 value at 1GHz.

Frequency (GHz)

requires detailed knowledge about the electronic properties of the graphene layers integrated on top of the Si or SiN substrates as well as those at different graphene layers in multi-layer graphene structures. In addition, the performance of the proposed modulators has to be studied at high modulation speeds with the ability to shape the input signal. Previously different aspects of these devices were characterized at different locations within the Georgia Tech campus as there was no experimental facility with all the required equipment for all the required characterization, which did not allow for the needed simultaneous measurement of different parameters of the devices. The developed characterization testbed has solved this issue by enabling to perform a complete high-speed characterization using different characterization configurations. This high-speed characterization will be also very useful for another pending proposal submitted to ARO for he high-speed characterization of optoelectronic properties of 2D heterostructure materials.

III.D. Role of the Developed test setup in other DoD-funded projects

The developed testbed has also greatly enhanced our characterization capability for several other projects on campus. Due to its importance for multiple projects, a separate lab in Adibi's group is dedicated to this testbed, and the lab will be made accessible to other researchers on-campus. Both Georgia Tech and Georgia Tech Research Institute have strong DoD-funded research portfolios in the areas of photonics, electronics, and optoelectronics, and the presence of this comprehensive characterization testbed will be highly beneficial for a large range of researchers involved in these projects. Two of the other DoD-funded projects in Adibi's group that have and will benefit from this research are listed below:

1) Project Title: "A New Material and Device platform for Compact, High-gain Integrated Photonic Modulator Technology," funded by the Office of Naval Research (ONR), start date: 3/1/2015, duration 3 years; PI: Adibi, Co-PI: Eftekhar:

This ONR-funded project is focused on the development of high-gain modulators at high modulation speeds in hybrid silicon carbide/silicon nitride (SiC/SiN) and double-layer SiC material platforms. This project will heavily benefit from the proposed characterization testbed for both electronic characterization of the SiC layers and detailed investigation of the modulation performance (especially the modulation speed).

1) Project Title: "Nonlinear Optical Signal processing On Chip: A New Paradigm for Implementation of Optical logic Functionality," funded by the Air Force Office of Scientific Research (AFOSR), start date: 9/1/2015, duration 3 years; PI: Adibi, Co-PI: Eftekhar:

The AFOSR-funded project is focused on the development of the foundation for a new digital signal processing/computing platform in the optical domain through the development of innovative high-speed and low-power nonlinear optical processing cores that can be co-integrated with digital signal processors to enable new functionalities such as very-high-speed signal processing and direct optical signal processing. The core material platform for this project is hybrid Si/SiN-based materials with potential infiltration with nonlinear optical polymer. Most of the devices that form the infrastructure for the proposed nonlinear signal processing functionalities have to operate at ultrahigh speeds, and they require a reliable testbed for the characterization of their optoelectronic properties. Thus, the AFOSR-funded project will considerably benefit from the availability of the proposed testbed in this DURIP proposal.

III.E. Final quotations of the purchased equipment

KEYSIGHT TECHNOLOGIES		Customer Refere	Customer Reference					
	GHI	Quote for Georgia	Institute of Technolog	y				
TECHNOL	OGIES	Quotation Number	er Quotation	Date	Expiration Date			
	.00120	3028648-1	25-Oct-201	6	31-Oct-2016			
		Agreement Numb	er/Expires	Final Des	tination Country			
		GEORGIAIN-G88	98-01-DEC-16	United St	ates			
		Payment Terms		Incoterm	S			
		NET 30 DAYS		DDP Unit	ed States			
Attention: Ali Effekhar		<u>.</u>						
Customer Address:								
Georgia Institute of Technology		Account Manager						
ECE 801 Atlantic Dr NW ATLANTA GA 30318-5682		GABRIEL (GABE) Email:	gabe_martin@ke	evsight com				
		Letter.	gabo_maran@m	yoigin: ooini				
United States		Sales/Technical S						
		MICHAEL C LARS Telephone:	EN 1 866 650-9516					
		Email:	mike_larsen@ke					
				,				
Felephone: (404) 401-748	3							
Email: eftekhar@gate								
-nan egan								
Please Direct Inquiries/Send Pu	rchase Orders To:	Keysight Sales Off						
KEVIN NAHODYL	0	Keysight Technologi	es Inc. / US					
Email: usa_order	@keysight.com	PO Box 4026 Englewood CO 80155-4026						
		United States	JJ-4020					
		Sintod Otatoo						

ltem	Product Number/Description	Unit Price	Unit Adjustment	Unit Net Price	Quantity	Extended Price USD				
1	86100D Infiniium DCA-X Oscilloscope Mainframe Return to Keysight Warranty - 3 years Marketing Program 100 %	24,210.00	-24,210.00	0.00	1	0.00				
	Notes: "This is a one-time special offer that will not apply to any future order(s). The sale of products outlined in this document is predicated upon ordering the products and quantities as specified herein. Changes to product mix and/or quantities may affect the offer amounts."									
	86100D-ETR Enhanced trigger, 13 GHz BW, pattern and module trigger Regional Discount 38.8 %	8,637.00	-3,351.16	5,285.84	1	5,285.84				
	86100D-SIM InfinitiSim-DCA Waveform Transformation SW, Fixed Perpetual License Regional Discount 38.8 %	4,960.00	-1,924.48	3,035.52	1	3,035.52				
	86100D-092 Internal hard drive (default option) Purchase Agreement Discount 20 %	0.00	0.00	0.00	1	0.00				
	86100D-GPI GPIB Card Interface - Installed Purchase Agreement Discount 20 %	376.00	-75.20	300.80	1	300.80				
	Estimated Weeks Delivery: 5			Item	Net Total:	8,622.16				
2	N1045A 60 GHz 2/4 Port Electrical Remote Sampling Head Return to Keysight Warranty - 3 years	0.00	0.00	0.00	1	0.00				
	Purchase Agreement Discount 20 % N1045A-02F 2 Channel Remote Head, 1.85mm, Female Regional Discount 38.8 %	46,923.00	-18,206.12	28,716.88	1	28,716.88				
	Notes: ***Special discount applied. See terms and conditions	below.***								

Quotation



Customer Reference	
Quote for Georgia Institute of Technology	
Quotation Number	Quotation Date
3028648-1	25-Oct-2016

ltem	Product Number/Description	Unit Price	Unit Adjustment	Unit Net Price	Quantity	Extended Price USD
	N1045A-LOJ Ultra-low Jitter Performance Purchase Agreement Discount 20 %	0.00	0.00	0.00	1	0.00
	Estimated Weeks Delivery: 5			Item	Net Total:	28,716.88
3	M8195A Arbitrary Waveform Generator 65GSa/s Return to Keysight Warranty - 3 years Power cord, United States and Canada - 120V Purchase Agreement Discount 20 %	0.00	-561.60	-561.60	1	-561.60
	M8195A-16G Upgrade to 16 GSa Memory Regional Discount 38.8 %	21,497.00	-8,340.84	13,156.16	1	13,156.16
	Notes: ***Special discount applied. See terms and conditions	below.***				
	M8195A-SEQ Sequencer Regional Discount 38.8 %	5,385.00	-2,089.38	3,295.62	1	3,295.62
	M8195A-001 Arbitrary Waveform Generator, 1 Channel, 65 GSa/s	102,110.00	-39,618.68	62,491.32	1	62,491.32
	Regional Discount 38.8 % M8195A-SCD Standard Calibration Document Purchase Agreement Discount 20 %	0.00	0.00	0.00	1	0.00
	M8195A-BU2 Bundle consisting of one M9502A 2-slot AXIe Chassis with USB Option	9,000.00	-3,492.00	5,508.00	1	5,508.00
	Regional Discount 38.8 % M8195A-810 Matched Cable Pair for M8195A AWG, 2.92 mm	3,231.00	-1,253.63	1,977.37	1	1,977.37
	Regional Discount 38.8 %					
	Estimated Weeks Delivery: 8			Item	Net Total:	85,866.87
		Unit Price	Total			226,329.00
		Adjustme Total	nt Total		US	-103,123.09 D 123,205.91

Comments:

Special terms are included with this quotation since special discounts are being granted. Your concurrence with these special terms will be required with any resulting order under this quotation.

Products purchased under this quote must be placed on one purchase order and no products may be added at a later date. This is a one-time special discount that will not apply to any future order(s). In the event Keysight reduces the list price of a product on this quotation during the validity of this quotation or prior to shipment, the list price for such products will not be reduced.

The sale of products under this quotation will be governed by the Terms and Conditions of the agreement between Customer and Keysight Technologies, Agreement Number G8S98 ("Master Agreement"). Since special discounts are being granted under this quotation, products purchased under this quotation with special discounts will not be further discounted under the Master Agreement. The sale of products under this quotation is predicated upon ordering the products and quantities as specified on the quotation. Changes in the product mix and/or quantities may affect the discount percentage.

This quotation and any resulting purchase order are subject to the terms and conditions of Purchase Agreement G8S98. Products on this quote with zero (0) percent discount may be a Distribution Preferred Product available through Keysight's Authorized Distributors. A list of Distributors can be found at http://www.keysight.com/main/contactInformation.jspx?tmprop=TM&pageMode=PF&cc=US&Ic=eng

The Terms, Conditions and Discounts of the above Purchase Agreement apply to this quotation. This quotation does not extend the contractual End Date of the Purchase Agreement.

Issue Order to:

XSoptix, LLC 800 Village Walk #316 Guilford, CT 06437 Sales@xsoptix.com

Fax: 800 878-7282 Phone: 203-401-8093

F.O.B. Madison, CT (small, woman owned business) DUNS# 011138174 Cage Code - 3MQC6



Prepared By	Tom Mahoney	Quote Number	00007767
Phone	4043076486	Created Date	3/15/2017
-		Expiration Date	4/14/2017
For questions, quo	tes, orders and info: sales@xsoptix.com	Terms	Net 30
		Availability	2-8 weeks ARO
Contact Name	Reza (Ali) Eftekhar	Ship To Name	GA Tech
Email	eftekhar@gatech.edu		
NOTES:	Factory stock at the time of quoting.		

Quantity	Product	Product Description			Sales Price	Total Price
1.00	XPDV2320R-VM-FP	Finisar - 50 GHz single photodetector, si connector, dual wavelength 1310/1550n	\$4,396.00	\$4,396.00		
			Subtotal	\$4,396.00		
			Discount	0.00%		
			Total Price	\$4,396.00		

Grand Total

\$4,396.00



Customer Contact Details

Contact Name:	Mr. Tianren Fan	Cor
Telephone:	4044020895	Tele
Email:	tianren.fan@gatech.edu	Em
Company:	GEORGIA INSTITUTE OF	Cor
Address:	TECHNOLOGY 711 Marietta Street Atlanta	Ado
	GA 30332 United States	Equ Ret Ado
Account No:	G209	

Quotation for New Test Equipment

Quotation No:	RUNQ88293-0
Quotation Date:	November 1, 2016
Expiration Date:	December 1, 2016
Payment Terms:	30 Days (Subject to Credit Approval)
Reference No:	

Microlease Contact Details

Contact Name:	Maria Macias
Telephone:	510-264-0887
Email:	maria.macias@microlease.com
Company: Address:	Microlease 25841 Industrial Blvd., Suite 200 Hayward California 94545
Equipment Return Address:	9221 Globe Center Drive, Suite 105 Morrisville North Carolina 27560 United States

Thank you for the opportunity to quote for the purchase of test equipment. Microlease provides a complete range of test equipment products and services. We sell, rent, lease, and buy test and measurement equipment as well as offer a full range of Asset Management services and solutions.

We believe you will find our prices competitive and we back our test equipment with quality and service few suppliers can match.

Product Details

Item	Manufacturer	Model	Description	List Price	Net Price	Qty	Line Total (USD)
1	Keithley	2614B Estimated Delivery: Stock Warranty: Manufacture		\$8,600.00 Sub 1	\$6,364.00 Item Total: Total (USD)	1	\$6,364.00 \$6,364.00 \$6,364.00
				G	Grand Total		\$6,364.00

Terms & Conditions of Sale:

https://www.microlease.com/us/termsandreturns?key=distributionterms



Que	otation for New Test Equipment
Quotation No:	RUNQ92093-2
Quotation Date:	December 27, 2016
Expiration Date:	January 26, 2017
Payment Terms:	30 Days (Subject to Credit Approval)

Customer Contact Details

Contact Name:	Mr. Tianren Fan	Contact Name:	Maria Macias
Telephone:	4044020895	Telephone:	510-264-0887
Email:	tianren.fan@gatech.edu	Email:	maria.macias@microlease.com
Company: Address:	GEORGIA INSTITUTE OF TECHNOLOGY 711 Marietta Street Atlanta GA 30332	Company: Address:	Microlease 25841 Industrial Blvd., Suite 200 Hayward California 94545
Account No:	G209	Equipment Return Address:	9221 Globe Center Drive, Suite 105 Morrisville North Carolina 27560 United States

Reference No:

Microlease Contact Details

Thank you for the opportunity to quote for the purchase of test equipment. Microlease provides a complete range of test equipment products and services. We sell, rent, lease, and buy test and measurement equipment as well as offer a full range of Asset Management services and solutions.

We believe you will find our prices competitive and we back our test equipment with quality and service few suppliers can match.

Product Details

ltem	Manufacturer	Model	Description	List Price	Net Price	Qty	Line Total (USD)
1	Keithley	8606	High Performance Modular Probe Kit	\$67.00	\$49.58	2	\$99.16
		Promotions:					
		Educational Discour	ıt				
		Estimated Delivery:	6.00 weeks		Item Total:		\$99.16
		Warranty: Manufa	cturer's Warranty		item Total:		\$55.10
2	Keithley	2600-BAN	Banana Jack Interface Cable for 2600 Series	\$183.00	\$135.42	2	\$270.84
		Options Fitted: BAN					
		Promotions:					
		Educational Discour	ıt				
		Estimated Delivery:	Stock Item		Item Total:		\$270.84
		Warranty: Manufa	cturer's Warranty		item rotai:		3210.04
3	Keithley	2600-TRIAX	Triax Adapter for 2600 Series	\$300.00	\$222.00	2	\$444.00
		Promotions:					
		Educational Discoun	it				
		Estimated Delivery:	Stock Item		Item Total:		\$444.00
		Warranty: Manufa	cturer's Warranty		item rotai:		3444.00
		wananty. wanula	curers warranty				
			page 1 of 2		micr		



Quotation for New	Test Equipment
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Quotation No:	RUNQ92093-2
Quotation Date:	December 27, 2016
Expiration Date:	January 26, 2017
Payment Terms:	30 Days (Subject to Credit Approval)
Reference No:	

Product Details

Item Manufacturer	Model	Description	List Price	Net Price	Qty	Line Total (USD)
			Sub T	otal (USD)		\$814.00
			G	rand Total		\$ 814.00
Terms & Conditions of S	ale:	https://www.microlease.com/us/terms	andreturns?ke	y=distribut	iontern	าร

page 2 of 2





Stone Mountain, GA 30087 kevinm@eoxsales.com

Quotation

Quotation To: Date Quote # GIT KM053017 Terms Amir Hosseninnia 5/30/17 Net 30 a.hosseinnia@gatech.edu Georgia Tech Validity Ship Via Cust Ref 778 Atlantic DR Room 252 30 Days 1050 B/W Atlanta GA 30332 Delivery 4 DAYS ARO F.O.B. Point FCA Factory 4047299803 Quantity Description Unit Price Extension Item 2 1 i50-GS-150 \$1,150.00 \$1,150.00 50 GHz Infinity probe, GSG, GS, SG 20% GIT Discount -\$429.00 Total: \$1,716.00

n, and are set

Please make your purchase order out to:

Cascade Microtech 9100 SW Gemini Dr Beaverton, OR 97006 FAX (503) 601-1002

Kevin Mays Kevin Mays

Name:

Net 30 Upon Approved Credit
 Prices quoted are for products with the ultimate destination within the United States, Mexico, or South America. If the product's ultimate destination is outside the U.S. Mexico, or South America, this quotation is void. Please contact Cascade Microtech, CM_Sales@cmicro.com, for correct pricing.
 Please note Cascade Microtech has factories in both Oregon, USA and Sacka, Germany.
 If agreeable, please list "Partial Okay and Early Delivery Acceptable" on your purchase order.
 Any purchase of Cascade Microtech products and/or services stated in this quotation is expressly limited to, and expressly made conditional on, customer's acceptance of Cascade Microtech's Terms and Conditions of Sale (available at: http://www.cmicro.com/company/legal-information/terms-and-conditions/cascade-microtech-terms-and-conditions-of-sale). Cascade objects to and rejects any different or additional terms contained in this purchase order, unless agreed to in writing by Cascade.



RF Components on Demand 1130 Junction Drive #100 Allen, TX 75013 Web: www.fairviewmicrowave.com Phone: 972-649-6678 Fax: 972-649-6689 Email: sales@fairviewmicrowave.com

Sales Quote No	Date
FMSQ24931	7/6/2017
Page(s)	1
Federal ID #272610210	

Cage Code #3FKR5

SALES QUOTATION

PLEASE REMIT PAYMENT TO: Fairview Microwave, Inc., PO Box 205405, Dallas, TX 75320-5405

Bill To: GEORGIA INSTITUTE OF TECHNOLOGY 778 Atlantic Dr., Rm 252 ATLANTA, GA 30332 USA Ship To: GEORGIA INSTITUTE OF TECHNOLOGY TIANREN FAN 778 Atlantic Dr., Rm 252 ATLANTA, GA 30318 USA

			Quote			
Sales Person	F.O.B.	Terms	Validity	Ship Via	Freight Terms	Reference No
Anthony Cerda	Origin	NET 30 DAYS	8/5/2017	2day	Prepaid	RFQ

Contact	Contact Email Address Phone No.		No.	Fax No.	Customer No.			
TIANREN FA	N	tianren.fan@gatech.ed	u	(404) 402-	-0895		FMC108258	
	Cable		HTS No. /					
Item No.	UOM	Description	ECCN Code	UOM	Quantity	Unit Price	Total Price	
SPA-180-37-01-SMA-		300 MHz to 18 GHz, Medium Power	8536.50.9065	EA	1	4,999.00	4,999.00	
A		Broadband Amplifier with 1 Watt, 37	EAR99					
		dB Gain and SMA						
Delivery: Ships within 2 FOB: Allen, TX.	4 hours af	ter receipt oforder.						
 Complete shipping a Payment Terms Net FOB: Allen, TX. (origi Shipping method (a 	30 days or n)	-						
Products adhere to the most current specifications available on the Fairview website at www.fairviewmicrowave.com.								
Thank you for conside	ring Fairvie	w for your all RF, microwave and millime	ter-wave product	requirements. Sh	nould you			
have any additional questions, please do not hesitate to contact our sales department.								
Thank you,								



RF Components on Demand 1130 Junction Drive #100 Allen, TX 75013 Web: www.fairviewmicrowave.com Phone: 972-649-6678 Fax: 972-649-6689 Email: sales@fairviewmicrowave.com

Sales Quote No	Date
FMSQ24932	7/6/2017
Page(s)	1
Federal ID #272610210	

Cage Code #3FKR5

SALES QUOTATION

PLEASE REMIT PAYMENT TO: Fairview Microwave, Inc., PO Box 205405, Dallas, TX 75320-5405

Bill To: GEORGIA INSTITUTE OF TECHNOLOGY 778 Atlantic Dr., Rm 252 ATLANTA, GA 30332 USA Ship To: GEORGIA INSTITUTE OF TECHNOLOGY TIANREN FAN 778 Atlantic Dr., Rm 252 ATLANTA, GA 30332 USA

Sales Person	F.O.B.	Terms	Quote Validity	Ship Via	Freight Terms	Reference No
Vincent Banh	Origin		8/5/2017	UPS Next Day Air Saver®	Prepaid	RFQ

Contact		Email Address	Phone No.		Fax No.	Customer No.	
TIANREN FA	AN	tianren.fan@gatech.ed	u	(404) 402-0895		FMC108258
	Cable		HTS No. /				
Item No.	UOM	Description	ECCN Code	UOM	Quantity	Unit Price	Total Price
SM3960		2.92mm Female to 1.85mm Male	8536.69.4010	EA	2	273.92	547.84
		Adapter	EAR99				
FMC3030988-06		1.85mm Male to 1.85mm Male Cable	8544.20.0000	EA	1	299.57	299.57
		RG405 Coax in 6 Inch	EAR99				
FMC3030988-09		1.85mm Male to 1.85mm Male Cable	8544.20.0000	EA	1	301.76	301.76
		RG405 Coax in 9 Inch	EAR99				
SM3952		SMA Male to 1.85mm Female Adapter	8536.69.4010	EA	2	143.53	287.06
			EAR99				

IN STOCK READY TO SHIP

Products purchased or received under these Terms and Conditions are subject to export control and economic sanctions laws, restrictions, regulations and orders of the United States. Customer agrees to comply with all applicable export control laws, restrictions and regulations of the United States and shall not export, or transfer for the purpose of re-export, any product to any embargoed country or region, including but not limited to Cuba, the Crimean Region of Ukraine, Iran, North Korea, Sudan, and Syria, or to any denied, blocked, or designated person or entity as mentioned in any such United States or EU law or regulation. Customer represents and warrants that it is not on the Denied Persons, Specially Designated Nationals or Debarred Persons List (as identified by the U.S. Treasury Office of Foreign Asset Control (OFAC) and by the U.S. Department of Commerce, Bureau of Industry and Security (BIS), or any other United States so ther law from purchasing the products or services hereunder. Customer shall be solely responsible to obtain any license to export, re-export, re-export or import as may be required. Customer also agrees that it will not use these products in connection with the proliferation of weapons of mass destruction, including missiles, nuclear, chemical or biological weapons.

All Purchase Orders are subject to final	By placing an order for products from Fairview, or by	Subtotal:	1,436.23
acceptance by Fairview Microwave Inc.	accepting delivery of products described on the	Total Sales Tax:	0.00
Fairview Microwave Inc. Terms and	applicable packing slip, bill of lading and/or invoice received	Freight:	0.00
Conditions of Sale posted on its website	with the products, you agree to be bound by and accept		
at www.fairviewmicrowave.com apply.	Fairview Terms and Conditions of Sale.	Total:	1,436.23

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	Part Number: Package Weigł	S7FC1013S - <u>Ask a technic</u> nt: 7.23 lbs / Each	al question	Drawings and Docum Auto CAD PDF	ents: 📆 🔂 と
	Avai ab e / Ships:	3-5 Days		Auto CAD DXF	🔬 🔂 🛛
	RoHS:	Rohsy		Solidworks	🚳 🔂 🖄
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	Release Date:	Qty 1 Add To Ca Sep 22, 2009	art	Step	🔬 🖻 🖻
⊕ Zoom		•		Manual:	1 <u>0</u>
Complete Product Details	ls 🛧			Software Download:	4
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				Building a Setup? One-Click download of multiple documents available from the shopping cart. No purchase necessary. Warranty (Subject to our General Terms an Conditions)	
				Two year warranty. Inc. are warrantied for the li- the extent applicable) t stated in the specificati	

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